

WoDiM 2010 First Call for Papers

*16th Workshop on Dielectrics in Microelectronics
June 28 – 30, 2010, Bratislava, Slovakia
AVS Sponsored Topical Conference*



Scope of the Workshop

New challenges offered by the application of dielectric materials in microelectronics will be discussed during the 16th Workshop on Dielectric Materials, WoDiM 2010. The goal of the WoDiM 2010 conference is to create a stimulating international platform for application-oriented scientists to exchange ideas and the latest experimental results covering the physics, technology and characterisation of dielectric materials in silicon integrated circuits.

Topics

Emerging dielectric materials, technologies and new device approaches

Theory of dielectric materials, interface science of dielectrics in contact with semiconductors & metals
Advanced technologies for thin dielectric film growth (ALD, MOCVD, PLD, MBE,...)
Characterisation of dielectrics with high sensitivity & spatial resolution, characterisation at nano-scale
Multiferroics, 2-DEG at dielectric interfaces, emerging dielectric materials
Novel oxide-based approaches to engineer SOI and GOI wafers

Dielectrics for aggressively scaled CMOS and other field effect devices

High-k dielectrics on Si
High-k dielectrics on high mobility semiconductors: Ge, III-V, III-N
High-k/metal gate stack, characterisation, scaling, stability
Defect characterisation, engineering of dielectrics, leakage currents
Electrical characterisation and reliability of devices with alternative dielectrics

Dielectrics for memory applications

High-k dielectrics for MIM (DRAM etc.)
Resistive switching in dielectrics
Dielectrics for non-volatile memories (flash, nanocrystal-based memories,...)
Ferroelectrics

Important dates

Submission of abstracts:	March 31, 2010
Notification of abstracts acceptance:	April 30, 2010
Conference registration (reduced rate):	May 1 - 31, 2010
Accommodation reservation:	May 1 - 31, 2010
Full length paper submission:	June 1, 2010
Conference:	June 28 – 30, 2010

Invited speakers

Bibes, M., CNRS/Thales and University Paris-Sud, Orsay, France
Dimoulas, A., Institute of Materials Science, NCSR Demokritos, Athens, Greece
Frank, M. M., IBM, Yorktown Heights, New York, USA
Hashizume, T., Hokkaido University, Sapporo, Japan
Kaczer, B., IMEC, Leuven, Belgium
Kummel, A. C., University of California, San Diego, La Jolla, California, USA
Lucovsky, G., NC State University, Raleigh, North Carolina, USA
Paskaleva, A., ISSP, Sofia, Bulgaria,
Ritala, M., University of Helsinki, Helsinki, Finland
Schlom, D. G., Penn State University, Pennsylvania, USA
Waser, R., RWTH Aachen, Aachen, Germany
Wenger, Ch., IHP, Frankfurt (Oder), Germany,
Zubko, P., University of Geneva, Geneva, Switzerland

Publications

Accepted papers will be published in The Journal of Vacuum Science and Technology B

Conference Fee

The conference office kindly requests participating scientists to pay the following fee:

Before May 31, 2010: 400 €

After May 31, 2010: 450 €

Reduced fee of 300 € is foreseen for PhD students.

A fee of 300 € is requested for accompanying guests not joining the scientific program of WoDiM 2010.

The following conference services are included in the conference fee of participating scientists:

- WoDiM 2010 conference (guest speakers, conference booklet, JVST B publication charge, coffee breaks etc.)
- Lunch & dinner during the Conference
- Social program (conference dinner & excursion)

We are grateful to the following sponsors of the WoDiM 2010



WoDiM 2010

will be organized by the Institute of Electrical Engineering, SAS, Bratislava

Conference web-page: <http://www.wodim2010.sk>

